

ABSTRACT OF THE DISCLOSURE

PLASMA ETCHING METHOD

5 There is provided a plasma etching method. The
plasma etching method includes generating plasma, by
using a first high frequency power output from a first
high frequency power supply, from a first processing gas
that contains fluorine-containing gas, thereby etching
10 a laminated film of a silicon oxide film and a silicon
nitride film through the generated plasma, and generating
plasma, by using the first high frequency power, from a
second processing gas that contains bromine-containing
gas, thereby etching the laminated film through the
15 generated plasma.

Fig. 4